## 2SB1012(K)

## Silicon PNP Epitaxial

## HITACHI

## Application

Low frequency power amplifier complementary pair with 2SD1376(K)

## Outline

TO-126 MOD


## 2SB1012(K)

Absolute Maximum Ratings $\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)$

| Item | Symbol | Rating | Unit |
| :---: | :---: | :---: | :---: |
| Collector to base voltage | $\mathrm{V}_{\text {cво }}$ | -120 | V |
| Collector to emitter voltage | $\mathrm{V}_{\text {ceo }}$ | -120 | V |
| Emitter to base voltage | $\mathrm{V}_{\text {EBO }}$ | -7 | V |
| Collector current | $\mathrm{I}_{\mathrm{c}}$ | -1.5 | A |
| Collector peak current | $\mathrm{I}_{\text {cpoeak }}$ | -3.0 | A |
| Collector power dissipation | $\mathrm{P}_{\mathrm{c}}{ }^{\text {1 }}$ | 20 | W |
| Junction temperature | Tj | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | Tstg | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |
| C to E diode forward current | $\mathrm{I}_{0}{ }^{\text {¹ }}$ | 1.5 | A |

## Electrical Characteristics $\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)$

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Collector to emitter breakdown voltage |  | -120 | - | - | V | $\mathrm{I}_{\mathrm{c}}=-10 \mathrm{~mA}, \mathrm{R}_{\text {BE }}=\infty$ |
| Emitter to base breakdown voltage | $\mathrm{V}_{\text {(BR)EBO }}$ | -7 | - | - | V | $\mathrm{I}_{\mathrm{E}}=-50 \mathrm{~mA}, \mathrm{I}_{\mathrm{c}}=0$ |
| Collector cutoff current | $\mathrm{I}_{\text {сво }}$ | - | - | -100 | $\mu \mathrm{A}$ | $\mathrm{V}_{\text {CB }}=-120 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0$ |
|  | $\mathrm{I}_{\text {ceo }}$ | - | - | -10 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{CE}}=-100 \mathrm{~V}, \mathrm{R}_{\mathrm{BE}}=\infty$ |
| DC current transfer ratio | $\mathrm{h}_{\text {FE }}$ | 2000 | - | 30000 |  | $\mathrm{V}_{\mathrm{CE}}=-3 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=-1 \mathrm{~A}^{* 1}$ |
| Collector to emitter saturation voltage | $\mathrm{V}_{\text {cE(say) }}$ | - | - | -1.5 | V | $\mathrm{I}_{\mathrm{c}}=-1 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=-1 \mathrm{~mA}^{* 1}$ |
|  | $\mathrm{V}_{\text {cE(say) }}$ | - | - | -2.0 | V | $\mathrm{I}_{\mathrm{C}}=-1.5 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=-1.5 \mathrm{~mA}^{* 1}$ |
| Base to emitter saturation voltage | $\mathrm{V}_{\text {BE[san) }}$ | - | - | -2.0 | V | $\mathrm{I}_{\mathrm{C}}=-1 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=-1 \mathrm{~mA}^{* 1}$ |
|  | $\mathrm{V}_{\text {BE(sav) } 2}$ | - | - | -2.5 | V | $\mathrm{I}_{\mathrm{C}}=-1.5 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=-1.5 \mathrm{~mA}^{* 1}$ |
| C to E diode forward voltage | $\mathrm{V}_{\mathrm{D}}$ | - | - | 3.0 | V | $\mathrm{I}_{\mathrm{o}}=1.5 \mathrm{~A}^{* 1}$ |
| Turn on time | $\mathrm{t}_{\text {on }}$ | - | 0.5 | - | $\mu \mathrm{s}$ | $\mathrm{I}_{\mathrm{c}}=-1 \mathrm{~A}, \mathrm{I}_{\mathrm{B} 1}=-\mathrm{I}_{\mathrm{B} 2}=-1 \mathrm{~mA}$ |
| Turn off time | $\mathrm{t}_{\text {of }}$ | - | 2.0 | - | $\mu \mathrm{S}$ |  |

Note: 1. Pulse test





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## HITACHI

Hitachi, Ltd.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109
or further information write to: Hitachi America, Ltd. Semiconductor \& IC Div. 2000 Sierra Point Parkway Brisbane, CA. 94005-1835 USA
el: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH Electronic Components Group Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 293000 Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd 16 Collyer Quay \#20-00 Hitachi Tower Singapore 0104 Tel: 535-2100 Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071

